MA10705

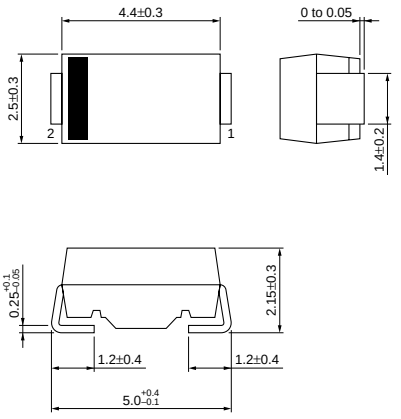
Silicon epitaxial planer type

For high-frequency rectification

■ Features

- New Mini-Power type package (2-pin)
- $I_{F(AV)}$=1.5A rectification possible
- Low V_F (forward voltage) type : V_F < 0.37V(at I_F=1.0A)

Unit : mm



1 : Anode
2 : Cathode
New Mini-Power Type Package (2-pin)

Marking Symbol : PK

■ Absolute Maximum Ratings (Ta= 25˚C)

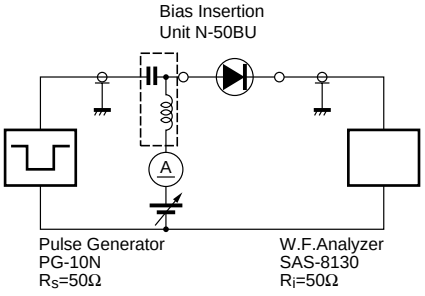
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	1.5	mA
Non-repetitive peak forward surge current	I_{FSM}*	30	A
Junction temperature	T_j	– 40 to + 125	˚C
Storage temperature	T_{stg}	– 40 to + 125	˚C

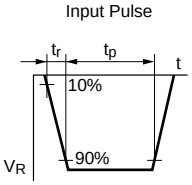
* 50Hz sine wave, one-cycle wave, high value (non-repetitive)

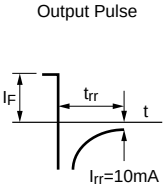
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 30V			3	mA
Forward voltage (DC)	V_F	I_F= 1.0A			0.37	V
Terminal capacitance	C_t	V_R= 10V, f =1MHz		90		pF
Reverse recovery time	t_{rr}*1,2	I_F = I_R =100mA I_{rr}= 0.1 · I_R, R_L= 100Ω			50	ns

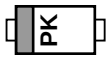
Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 20MHz
3. *1 Achieved with a printed-circuit board (glass epoxy)
*2 t_{rr} measuring circuit



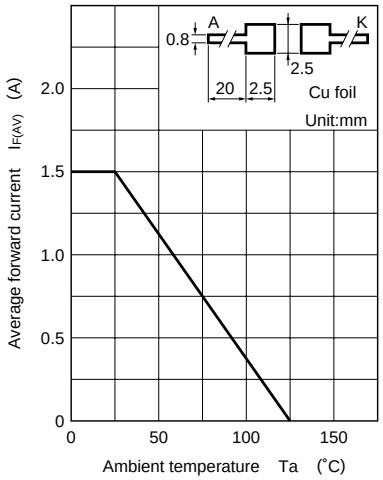




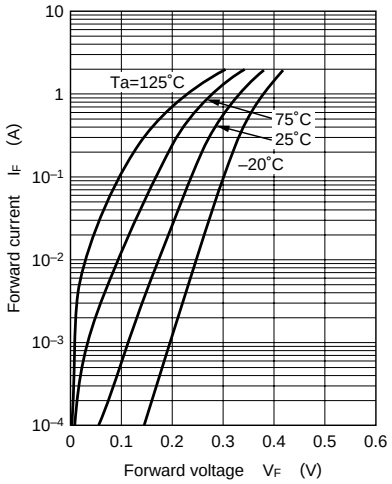
■ Marking



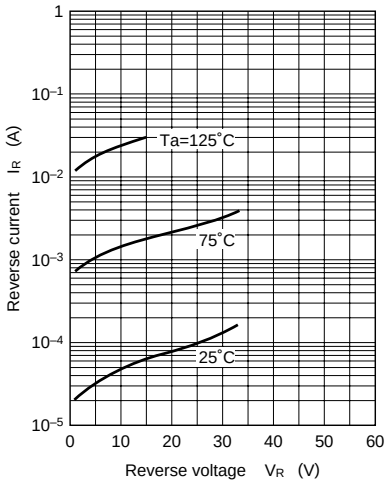
$I_{F(AV)} - Ta$



$I_F - V_F$



$I_R - V_R$



$C_t - V_R$